

# **TSM9434** 20V P-Channel MOSFET

50P-8	
5	

Pin Definition: 1. Source 2. Source 3. Source 4. Gate 5, 6, 7, 8. Drain

### PRODUCT SUMMARY

V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (mΩ)	I <sub>D</sub> (A)
20	40 @ V <sub>GS</sub> = -4.5V	-6.4
-20	60 @ V <sub>GS</sub> = -2.5V	-5.1

### **Features**

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

### **Application**

- Load Switch
- PA Switch

### **Ordering Information**

Part No.	Package	Packing
TSM9434CS RL	SOP-8	T&R

#### Absolute Maximum Rating (Ta = 25 °C unless otherwise noted)

Parameter Drain-Source Voltage		Symbol	Limit	Unit V	
		V <sub>DS</sub>	-20		
Gate-Source Voltage		V <sub>GS</sub>	±8	V	
Continuous Drain Current		I <sub>D</sub>	-6.4	А	
Pulsed Drain Current		I <sub>DM</sub>	±10	А	
Continuous Source Current (Diode Conduction) <sup>a,b</sup>		I <sub>S</sub>	-2.5	А	
Maximum Power Dissipation	Ta = 25 °C	P <sub>D</sub>	2.5	W	
	Ta = 70 °C		1.6		
Operating Junction Temperature		TJ	+150	°C	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	- 55 to +150	°C	

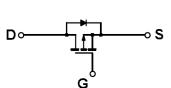
#### **Thermal Performance**

Parameter	Symbol	Limit	Unit
Junction to Case Thermal Resistance	Rθ <sub>JC</sub>	30	°C/W
Junction to Ambient Thermal Resistance (PCB mounted)	Rθ <sub>JA</sub>	50	°C/W

Notes:

a. Surface Mounted on 1" x 1" FR4 Board.

b. Pulse width limited by maximum junction temperature



**Block Diagram** 

P-Channel MOSFET



#### Ph COMF NCE

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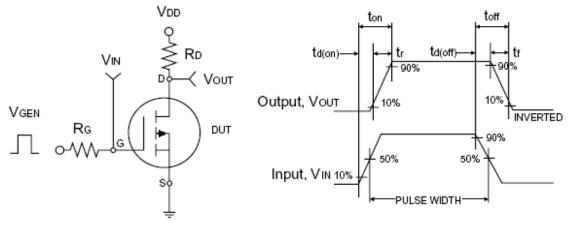
### **Electrical Specifications**

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static		1			I	
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_{D} = -250uA$	BV <sub>DSS</sub>	-20			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 uA$	V <sub>GS(TH)</sub>	-0.4		-1.0	V
Zero Gate Voltage Drain Current	$V_{DS}$ = -16V, $V_{GS}$ = 0V	I <sub>DSS</sub>			-1.0	uA
Gate Body Leakage	$V_{GS}$ = ±8V, $V_{DS}$ = 0V	I <sub>GSS</sub>			±100	nA
On-State Drain Current	V <sub>DS</sub> ≤-5V, V <sub>GS</sub> = -4.5V	I <sub>D(ON)</sub>	-10			А
Drain-Source On-State Resistance	$V_{GS}$ = -4.5V, $I_{D}$ = -6.4A	D		31	40	mΩ
	$V_{GS}$ = -2.5V, $I_{D}$ = -5.1A	R <sub>DS(ON)</sub>		45	60	
Forward Transconductance	$V_{DS}$ = -9V, $I_{D}$ = -6.4A	<b>g</b> <sub>fs</sub>		14		S
Diode Forward Voltage	I <sub>S</sub> = -2.5A, V <sub>GS</sub> = 0V	V <sub>SD</sub>		- 0.9	-1.2	V
Dynamic <sup>♭</sup>						
Total Gate Charge	V <sub>DS</sub> = -10V, I <sub>D</sub> = -6.4A,	Qg		12.5	19	
Gate-Source Charge		Q <sub>gs</sub>		1.7		nC
Gate-Drain Charge	- V <sub>GS</sub> = -4.5V	$Q_{gd}$		3.3		
Input Capacitance		C <sub>iss</sub>		1020		
Output Capacitance	V <sub>DS</sub> = -10V, V <sub>GS</sub> = 0V, f = 1.0MHz	C <sub>oss</sub>		191		pF
Reverse Transfer Capacitance		C <sub>rss</sub>		140		
Switching <sup>C</sup>						
Turn-On Delay Time		t <sub>d(on)</sub>		25	40	
Turn-On Rise Time	$V_{DD} = -10V, R_L = 10\Omega,$	tr		43	65	
Turn-Off Delay Time	$I_{\rm D}$ = -1A, $V_{\rm GEN}$ = -4.5V,	t <sub>d(off)</sub>		71	110	nS
Turn-Off Fall Time	$-R_{\rm G}=6\Omega$	t <sub>f</sub>		48	75	]

Notes:

a. pulse test: PW  $\leq$ 300µS, duty cycle  $\leq$ 2% b. For DESIGN AID ONLY, not subject to production testing.

b. Switching time is essentially independent of operating temperature.



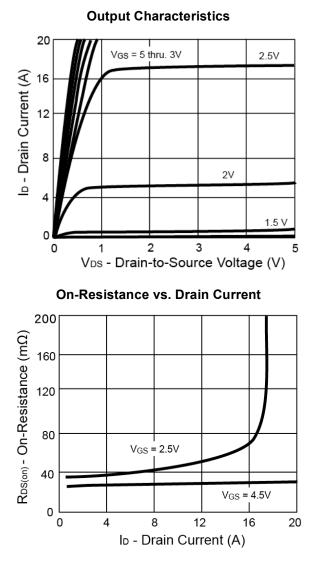
Switching Test Circuit

#### Switchin Waveforms

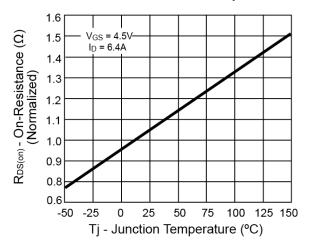


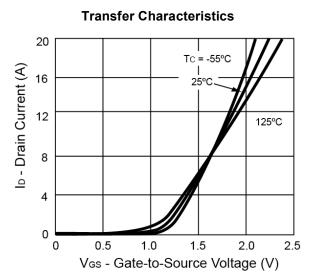
## **TSM9434** 20V P-Channel MOSFET

#### Electrical Characteristics Curve (Ta = 25 °C, unless otherwise noted)

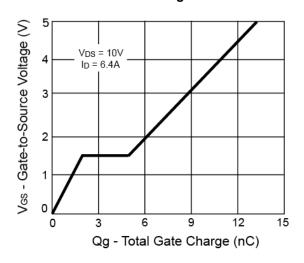


**On-Resistance vs. Junction Temperature** 

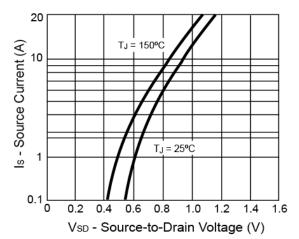




Gate Charge



Source-Drain Diode Forward Voltage





2

0

10<sup>-2</sup>

10-1

1

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#### Electrical Characteristics Curve (Ta = 25 °C, unless otherwise noted)

T<sub>A</sub> = 25°C

100

Ш

600

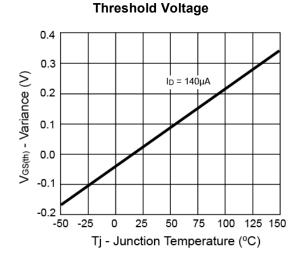
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10

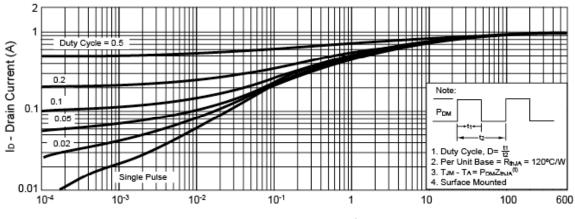
Tiime (sec)

### 0.15 $R_{DS(on)}$ - On-Resistance ( $\Omega$ ) 0.12 I<sub>D</sub> = 4.7A 0.09 $I_D = 2A$ 0.06 0.03 0 3 4 0 1 2 5 VGs - Gate-to-Source Voltage (V) **Single Pulse Power** 12 10 Power (W) 8 6 4

**On-Resistance vs. Gate-Source Voltage** 



#### Normalized Thermal Transient Impedance, Junction-to-Ambient

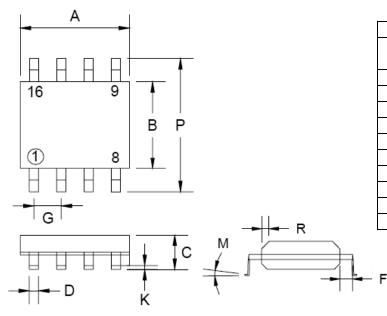


Square Wave Pulse Duration (sec)



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### **SOP-8 Mechanical Drawing**



SOP-8 DIMENSION					
DIM	MILLIMETERS		INCHES		
DIM	MIN	MAX	MIN	MAX.	
A	4.80	5.00	0.189	0.196	
В	3.80	4.00	0.150	0.157	
С	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.27BSC		0.05BSC		
K	0.10	0.25	0.004	0.009	
М	0°	7°	0°	7°	
Р	5.80	6.20	0.229	0.244	
R	0.25	0.50	0.010	0.019	



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